

MPC2105A
MPC2106A

512KB and 1MB BurstRAM™ Secondary Cache Modules for PowerPC™ PReP/CHRP Platforms

The MPC2105A and the MPC2106A are designed to provide burstable, high performance L2 cache for the PowerPC 60x microprocessor family in conformance with the PowerPC Reference Platform (PReP) and the PowerPC Common Hardware Reference Platform (CHRP) specifications. These products utilize synchronous data RAMs.

The MPC2105A and MPC2106A utilize synchronous BurstRAMs. The modules are configured as 64K x 72, and 128K x 72 bits in a 178 (89 x 2) pin DIMM format. The MPC2105A uses four of the 3 V 64K x 18; the MPC2106A uses eight of the 3 V 64K x 18. For tag bits, a 5 V cache tag RAM configured as 16K x 12 for tag field plus 16K x 2 for valid and dirty status bits is used.

Bursts can be initiated with the \overline{ADS} signal. Subsequent burst addresses are generated internal to the BurstRAM by the \overline{CNTEN} signal.

Write cycles are internally self timed and are initiated by the rising edge of the clock (CLKx) inputs. Eight write enables are provided for byte write control.

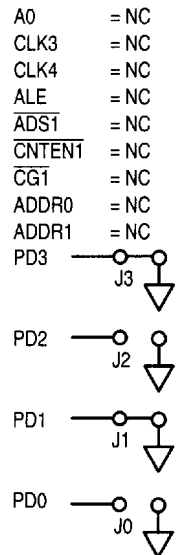
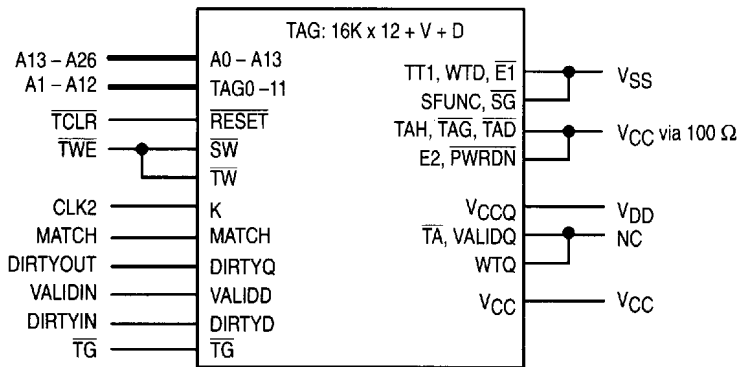
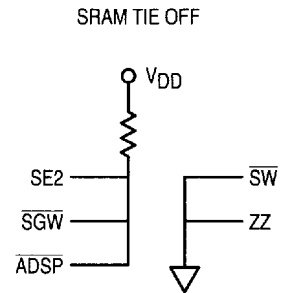
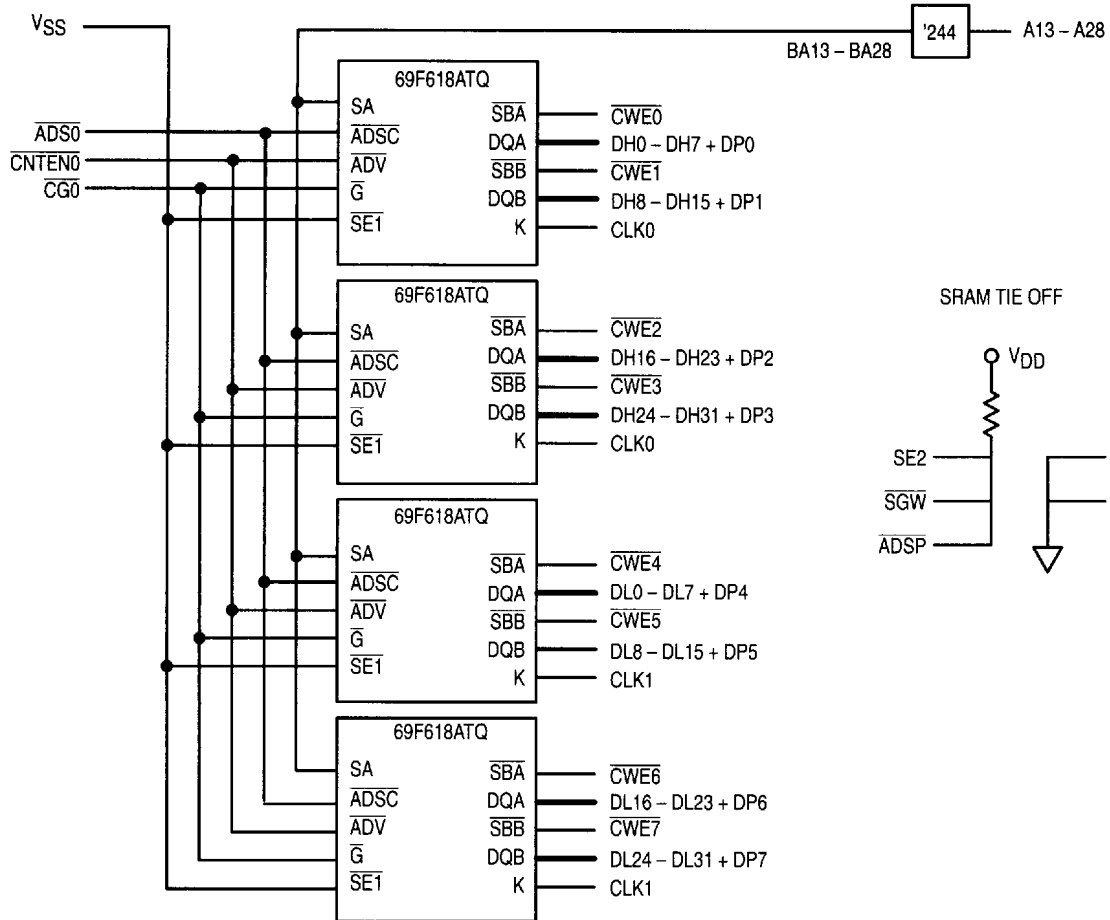
Presence detect pins are available for auto configuration of the cache control. A serial EEPROM is optional to provide more in-depth description of the cache module. This EEPROM will be available on future revisions of the module family.

The module family pinout will support 5 V and 3.3 V components for a clear path to lower voltage and power savings. Both power supplies must be connected.

All of these cache modules are plug and pin compatible with each other.

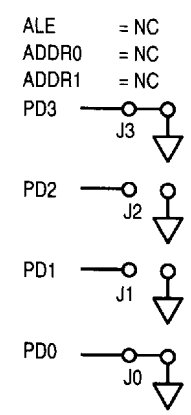
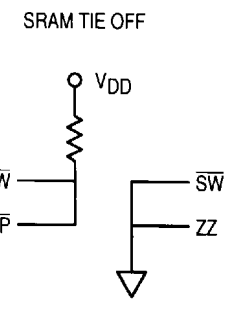
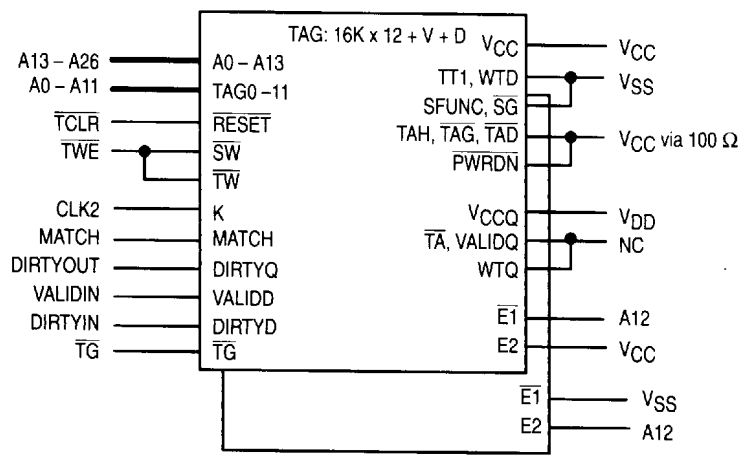
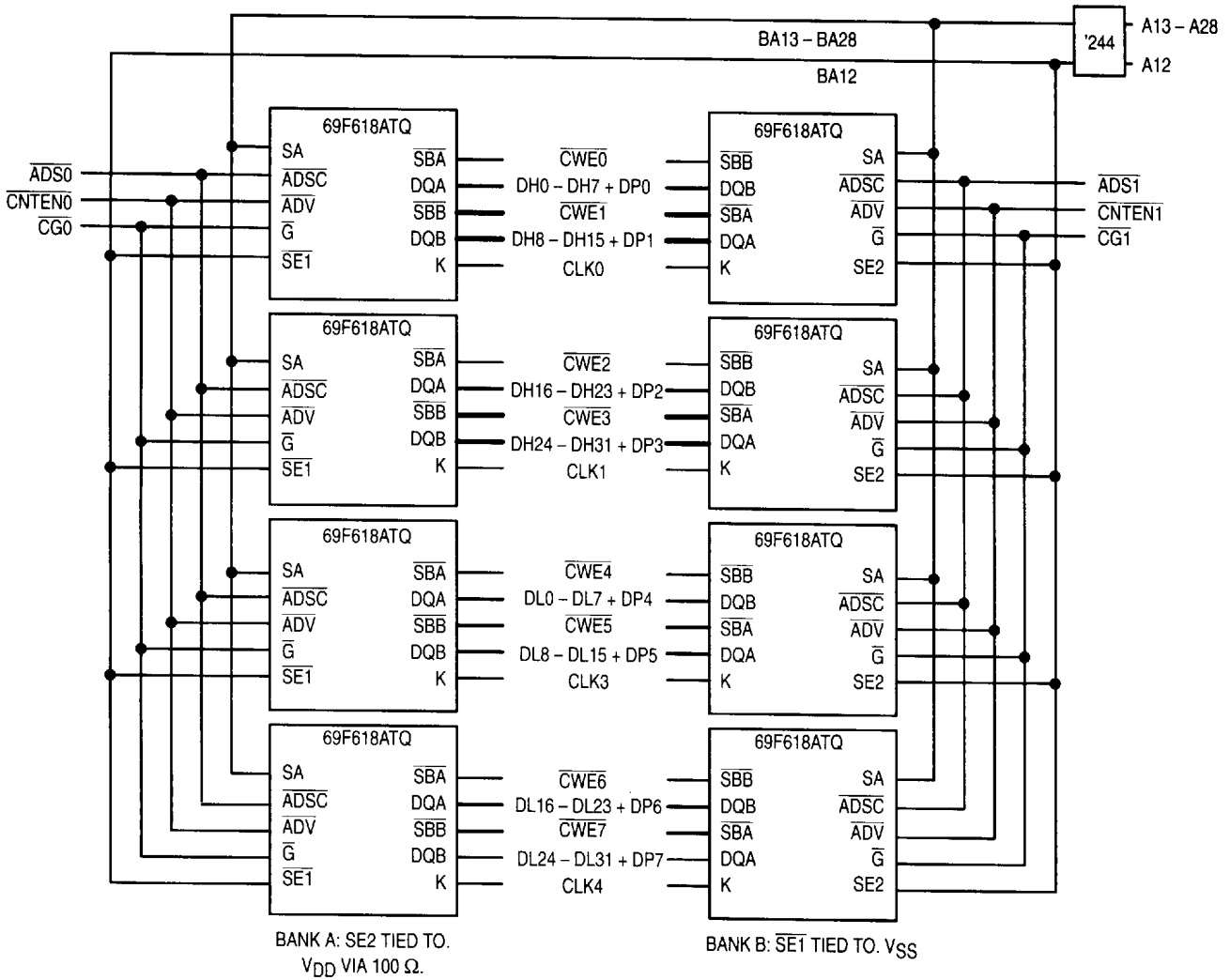
- PowerPC-style Burst Counter on Chip (MPC2105A/6A)
- Flow-Through Data I/O (MPC2105A/6A)
- Plug and Pin Compatibility
- Multiple Clock Pins for Reduced Loading
- 20 Ω Series Resistors on DL and DH Pins for Noise Reduction
- All Cache Data and Tag I/Os are LVTTL (3.3 V) Compatible (MPC2105/6)
- Three State Outputs
- Byte Write Capability
- Fast Module Clock Rates: Up to 66 MHz
- Fast SRAM Access Times: 10 ns for Tag RAM Match
9 ns for Data RAM
- Decoupling Capacitors for Each Fast Static RAM
- High Quality Multi-Layer FR4 PWB With Separate Power and Ground Planes
- 178 Pin Card Edge Module
- Burndy Connector, Part Number: ELF178KSC-3Z50

MPC2105A BLOCK DIAGRAM



Note: BA28 is tied to SA0 on SRAM;
 BA27 is tied to SA1 on SRAM;
 STANDBY is tied to $\overline{SE3}$ on SRAM.

MPC2106A BLOCK DIAGRAM



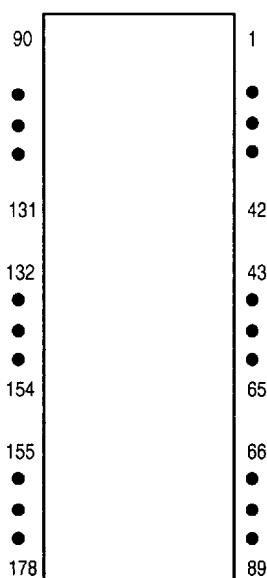
Note: BA28 is tied to SA0 on SRAM;
 BA27 is tied to SA1 on SRAM;
 STANDBY is tied to SE3 on SRAM.

PIN ASSIGNMENT 178-LEAD DIMM

Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
1	VSS	27	DH0	53	DL1	79	VSS	105	DH14	131	DL17	157	A22
2	PD0/IDSCCLK	28	DP0	54	DL0	80	A7	106	DH13	132	CWE6	158	A20
3	PD2	29	VSS	55	VSS	81	A5	107	VCC	133	DL15	159	VSS
4	DH30	30	CLK1	56	CLK2	82	A3	108	DH10	134	DL13	160	A18
5	DH28	31	VSS	57	VSS	83	A0	109	DH8	135	VSS	161	A16
6	DH26	32	DL28	58	DP4	84	VCC	110	CWE1	136	DL10	162	A15
7	DH24	33	DL26	59	CG0	85	TCLR	111	DH6	137	DL8	163	A14
8	VDD	34	DL24	60	CG1	86	MATCH	112	VDD	138	CWE5	164	VDD
9	DP3	35	DP7	61	VDD	87	TG	113	DH4	139	DL6	165	A10
10	DH22	36	VCC	62	ADDR0	88	DIRTYIN	114	VSS	140	VDD	166	A8
11	DH20	37	DL22	63	RESERVED	89	VSS	115	CLK0	141	DL5	167	A6
12	DH19	38	DL20	64	ADS0	90	VSS	116	VSS	142	DL2	168	VSS
13	VSS	39	DL18	65	ADS1	91	PD1/IDSDATA	117	DH1	143	VSS	169	A4
14	DH17	40	DL16	66	A28	92	PD3	118	CWE0	144	CLK3	170	A2
15	DP2	41	VSS	67	A26	93	DH31	119	DL31	145	VSS	171	A1
16	DH15	42	DP6	68	A25	94	DH29	120	DL30	146	CLK4	172	BURSTMODE
17	DH12	43	DL14	69	A23	95	DH27	121	VSS	147	VSS	173	VCC
18	VCC	44	DL12	70	VSS	96	DH25	122	DL29	148	CWE4	174	VALIDIN
19	DH11	45	DL11	71	A21	97	VDD	123	DL27	149	ALE	175	TWE
20	DH9	46	VSS	72	A19	98	CWE3	124	DL25	150	VDD	176	STANDBY
21	DP1	47	DL9	73	A17	99	DH23	125	VCC	151	ADDR1	177	DIRTYOUT
22	DH7	48	DP5	74	A13	100	DH21	126	CWE7	152	RESERVED	178	VSS
23	VDD	49	DL7	75	VDD	101	DH18	127	DL23	153	CNTEN0		
24	DH5	50	DL4	76	A12	102	VSS	128	DL21	154	CNTEN1		
25	DH3	51	VDD	77	A11	103	DH16	129	DL19	155	A27		
26	DH2	52	DL3	78	A9	104	CWE2	130	VSS	156	A24		

NOTE: VCC and VDD must be connected on all modules.

TOP VIEW – CASE TBD



PIN DESCRIPTIONS

Pin Locations	Symbol	Type	Description
66, 67, 68, 69, 71, 72, 73, 74, 76, 77, 78, 80, 81, 82, 83, 155, 156, 157, 158, 160, 161, 162, 163, 165, 166, 167, 169, 170, 171	A0 – A28	Input	Address Inputs – (MSB:0, LSB:28).
62	ADDR0	Input	Least significant address bit when asynchronous Data RAMs are used.
151	ADDR1	Input	Next to least significant address bit when asynchronous Data RAMs are used.
64, 65	$\overline{\text{ADS}}_0$, $\overline{\text{ADS}}_1$	Input	Data RAM Address Strobe – For MPC2105A use $\overline{\text{ADS}}_0$ only. For MPC2106A use $\overline{\text{ADS}}_0$, $\overline{\text{ADS}}_1$.
149	ALE	Input	Data RAM Address Latch Enable – Use for asynchronous Data RAM only.
172	BURSTMODE	Input	Burstmode. 0 = Linear, 1 = Interleaved.
59, 60	$\overline{\text{CG}}_0$, $\overline{\text{CG}}_1$	Input	Data RAM Output Enables – For MPC2105A use $\overline{\text{CG}}_0$ only. For MPC2106A use $\overline{\text{CG}}_0$, $\overline{\text{CG}}_1$.
30, 56, 115, 144, 146	CLK0 – CLK4	Input	Clock Inputs – CLK2 is for Tag RAM, CLK0, 1, 3, and 4 are for Data RAMs only. For MPC2106A use all the clocks. For MPC2105A use CLK0 – CLK2 only.
153, 154	$\overline{\text{CNTEN}}_0$, $\overline{\text{CNTEN}}_1$	Input	Data RAM Count Enables – For MPC2105A use $\overline{\text{CNTEN}}_0$ only. For MPC2106A use $\overline{\text{CNTEN}}_0$, $\overline{\text{CNTEN}}_1$.
98, 104, 110, 118, 126, 132, 138, 148	$\overline{\text{CWE}}_0$ – $\overline{\text{CWE}}_7$	Input	Data RAM Write Enables – (MSB:0, LSB:7).
4, 5, 6, 7, 10, 11, 12, 14, 16, 17, 19, 20, 22, 24, 25, 26, 27, 93, 94, 95, 96, 99, 100, 101, 103, 105, 106, 108, 109, 111, 113, 117	DH0 – DH31	I/O	High Data Bus – (MSB:0, LSB:31).
88	DIRTYIN	Input	Dirty input bit.
177	DIRTYOUT	Output	Dirty output bit.
32, 33, 34, 37, 38, 39, 40, 43, 44, 45, 47, 49, 50, 52, 53, 54, 119, 120, 122, 123, 124, 127, 128, 129, 131, 133, 134, 136, 137, 139, 141, 142	DL0 – DL31	I/O	Low Data Bus – (MSB:0, LSB:31).
9, 15, 21, 28, 35, 42, 48, 58	DP0 – DP7	I/O	Data Parity Bits – (MSB:0, LSB:7)
86	MATCH	Output	Tag RAM active high match indication.
2	PD0/IDSCCLK	Input	Presence detect bit 0/EEPROM serial clock. (EEPROM option only).
91	PD1/IDSDATA	I/O	Presence detect bit 1/EEPROM serial data. (EEPROM option only).
3, 92	PD2, PD3	Output	Presence detect bits.
63, 152	RESERVED		Reserved pin.
176	STANDBY	Input	Standby pin. Reduces standby power consumption.
85	$\overline{\text{TCLR}}$	Input	Tag RAM clear.
87	TG	Input	Tag RAM output enable.
175	$\overline{\text{TWE}}$	Input	Tag RAM write enable.
174	VALIDIN	Input	Tag RAM valid bit.
18, 36, 84, 107, 125, 173	VCC	Input	+ 5 V power supply. Must be connected.
8, 23, 51, 61, 75, 97, 112, 140, 150, 164	VDD	Input	+ 3.3 V power supply. Must be connected.
1, 13, 29, 31, 41, 46, 55, 57, 70, 79, 89, 90, 102, 114, 116, 121, 130, 135, 143, 145, 147, 159, 168, 178	VSS	Input	Ground.

DATA RAM MCM69F618A SYNCHRONOUS TRUTH TABLE (See Notes 1, 2, and 3)

STANDBY	ADS _x	CNTEN _x	CWEx	CLK _x	Address Used	Operation
H	L	X	X	L-H	N/A	Deselected
L	L	X	L	L-H	External Address	Write Cycle, Begin Burst
L	L	X	H	L-H	External Address	Read Cycle, Begin Burst
X	H	L	L	L-H	Next Address	Write Cycle, Continue Burst
X	H	L	H	L-H	Next Address	Read Cycle, Continue Burst
X	H	H	L	L-H	Current Address	Write Cycle, Suspend Burst
X	H	H	H	L-H	Current Address	Read Cycle, Suspend Burst

NOTES:

1. X means Don't Care.
2. All inputs except \overline{CG} must meet set-up and hold times for the low-to-high transition of clock (CLK0 – CLK4).
3. Wait states are inserted by suspending burst.

ASYNCHRONOUS TRUTH TABLE (See Notes 1 and 2)

Operation	\overline{CG}	I/O Status
Read	L	Data Out (DQ0 – DQ8)
Read	H	High-Z
Write	X	High-Z — Data In
Deselected	X	High-Z

NOTES:

1. X means Don't Care.
2. For a write operation following a read operation, \overline{CG} must be high before the input data required set-up time and held high through the input data hold time.

ABSOLUTE MAXIMUM RATINGS (Voltages Referenced to $V_{SS} = 0\text{ V}$)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{CC}	- 0.5 to + 7.0	V
Voltage Relative to V_{SS}	V_{in}, V_{out}	- 0.5 to $V_{CC} + 0.5$	V
Output Current (per I/O)	Data RAM Tag I_{out}	± 30 ± 20	mA
Power Dissipation	MPC2105A MPC2106A P_D	4.6 9.2	W
Temperature Under Bias	T_{bias}	- 10 to + 85	°C
Operating Temperature	T_A	0 to +70	°C
Storage Temperature	T_{stg}	- 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established.

This device contains circuitry that will ensure the output devices are in High-Z at power up.

DC OPERATING CONDITIONS AND CHARACTERISTICS

($V_{CC} = 5.0\text{ V} \pm 5\%$, $V_{DD} = 3.3\text{ V} \pm 10\%$, $T_A = 0\text{ to } +70^\circ\text{C}$, Unless Otherwise Noted)

RECOMMENDED OPERATING CONDITIONS (Voltages referenced to $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	V_{CC}	4.75	5.25	V
	V_{DD}	3.00	3.60	
Input High Voltage	V_{IH}	2.2	$V_{DD} + 0.3^{**}$	V
Input Low Voltage	V_{IL}	-0.5*	0.8	V

* V_{IL} (min) = -0.5 V dc; V_{IL} (min) = -2.0 V ac (pulse width $\leq 20\text{ ns}$) for $I \leq 20.0\text{ mA}$.

** V_{IH} (max) = $V_{DD} + 0.3\text{ V}$ dc; V_{IH} (max) = $V_{DD} + 2.0\text{ V}$ ac (pulse width $\leq 20\text{ ns}$) for $I \leq 20.0\text{ mA}$.

DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, $V_{in} = 0\text{ to } V_{DD}$)	Data RAM Tag $I_{kg}(I)$	—	± 1.0 ± 5.0	μA
Output Leakage Current ($\overline{CG} = V_{IH}$, $V_{out} = 0\text{ to } V_{DD}$)	Data RAM Tag $I_{kg}(O)$	—	± 1.0 ± 5.0	μA
TTL Output Low Voltage ($I_{OL} = +8.0\text{ mA}$)	V_{OL}	—	0.4	V
TTL Output High Voltage ($I_{OH} = -4.0\text{ mA}$)	V_{OH}	2.4	—	V

POWER SUPPLY CURRENTS

Parameter	Symbol	Max	Unit
AC Supply Current ($\overline{CG} = V_{IH}$, $E = V_{IL}$, $I_{out} = 0\text{ mA}$, All Inputs = V_{IL} and V_{IH} , $V_{IL} = 0.0\text{ V}$ and $V_{IH} \geq 3.0\text{ V}$, Cycle Time $\geq 20\text{ ns}$)	MPC2105A MPC2106A I_{DDA}	900 1800	mA
	MPC2105A MPC2106A I_{CCA}	320 640	mA
AC Standby Current ($E = V_{IH}$, $I_{out} = 0\text{ mA}$, All Inputs = V_{IL} or V_{IH} , $V_{IL} = 0.0\text{ V}$ and $V_{IH} \geq 3.0\text{ V}$, Cycle Time $\geq 20\text{ ns}$)	MPC2105A MPC2106A $I_{SB1}(V_{DD})$	440 880	mA
	MPC2105A MPC2106A $I_{SB1}(V_{CC})$	320 640	mA

CAPACITANCE ($f = 1.0\text{ MHz}$, $dV = 3.0\text{ V}$, $T_A = 25^\circ\text{C}$, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Typ	Max	Unit
Input Capacitance (A13 – A28) (Data RAM Control Pins) (CLK0 – CLK4) (Tag Control Pins)	C_{in}	—	15	pF
		16	20	
		8	10	
		—	5	
Tag Output Capacitance (MATCH, DIRTYOUT)	C_{out}	—	7	pF
Data RAM Input/Output Capacitance (DH0 – DH31, DL0 – DL31)	$C_{I/O}$	6	8	pF
Tag Input/Output Capacitance (A0 – A11)	$C_{I/O}$	—	7	pF

DATA RAMs AC OPERATING CONDITIONS AND CHARACTERISTICS
(V_{CC} = 5.0 V ± 5%, V_{DD} = 3.3 V ± 10% T_A = 0 to + 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V
Input Rise/Fall Time 3 ns

Output Timing Reference Level 1.5 V
Output Load See Figure 1A Unless Otherwise Noted

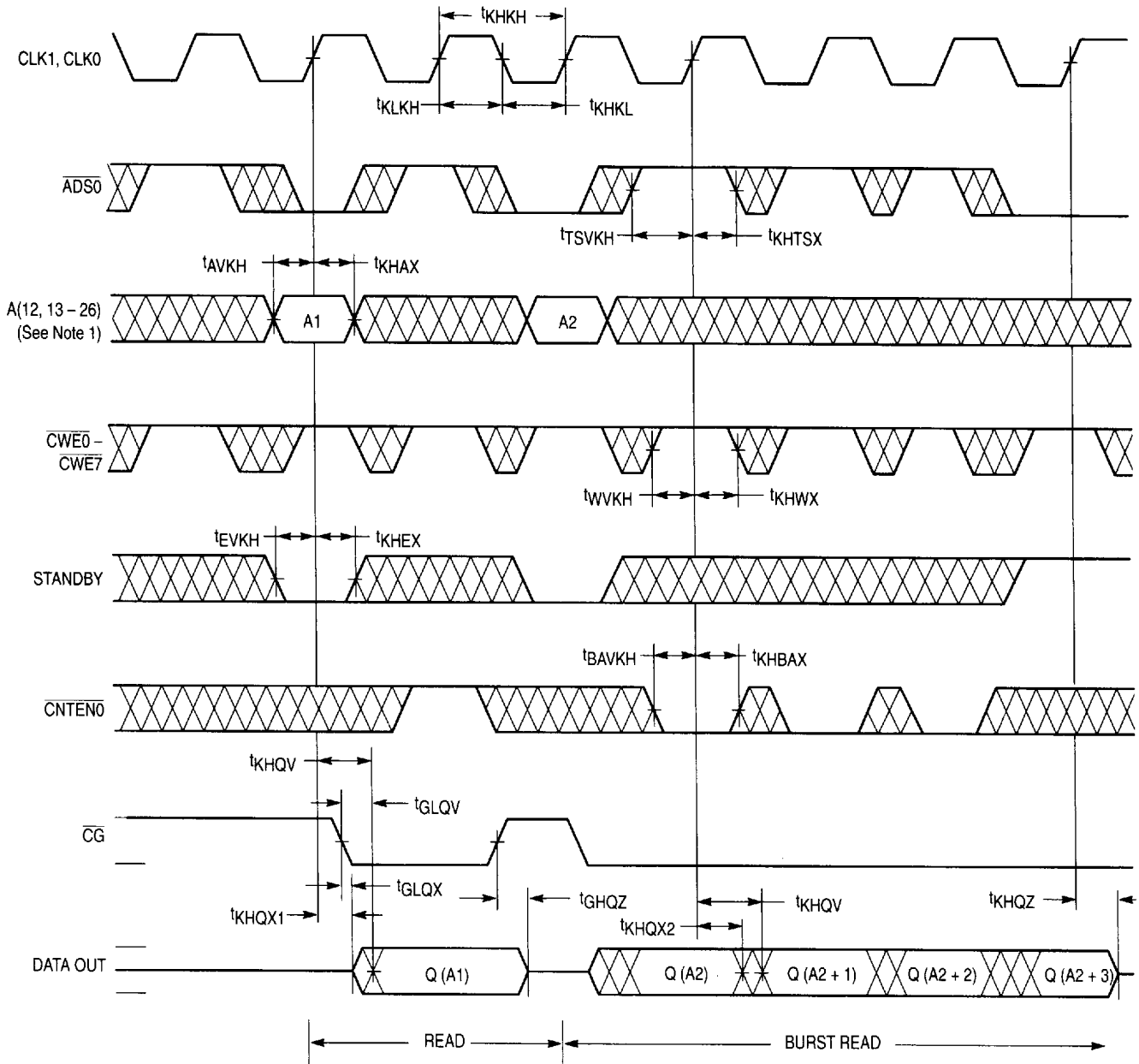
SYNCHRONOUS DATA RAMs READ/WRITE CYCLE TIMING (See Notes 1, 2, and 3)

Parameter	Symbol	MPC2105A MPC2106A		Unit	Notes	
		Min	Max			
Cycle Time	t _{KHKH}	15	—	ns		
Clock Access Time	t _{KHQV}	—	9	ns	4	
Output Enable to Output Valid	t _{GLQV}	—	5	ns		
Clock High to Output Active	t _{KHQX1}	6	—	ns		
Clock High to Output Change	t _{KHQX2}	3	—	ns		
Output Enable to Output Active	t _{GLQX}	0	—	ns		
Output Disable to Q High-Z	t _{GHQZ}	2	6	ns		
Clock High to Q High-Z	t _{KHQZ}	—	6	ns		
Clock High Pulse Width	t _{KHKL}	5	—	ns		
Clock Low Pulse Width	t _{KLKH}	5	—	ns		
Setup Time	Address	t _{AVKH}	7.5	—	ns	5, 6
Setup Times:	Address Status	t _{SVKH}	2.5	—	ns	5
	Data In	t _{DVKH}				
	Write	t _{WVKH}				
	Address Advance	t _{BAVVKH}				
	Chip Enable	t _{EVKH}				
Hold Times:	Address	t _{KHAX}	0.5	—	ns	5
	Address Status	t _{KHTSX}				
	Data In	t _{KHDX}				
	Write	t _{KHWX}				
	Address Advance	t _{KHBAX}				
	Chip Enable	t _{KHEX}				

NOTES:

1. In setup and hold times, W (write) refers to either one or both byte write enables \overline{LW} and \overline{UW} .
2. All read and write cycle timings are referenced from CLK or \overline{CG} .
3. \overline{CG} is a don't care when \overline{UW} or \overline{LW} is sampled low.
4. Maximum access times are guaranteed for all possible PowerPC external bus cycles.
5. This is a synchronous device. All addresses must meet the specified setup and hold times for **ALL** rising edges of CLK whenever \overline{TSP} or \overline{TSC} is low, and the chip is selected. All other synchronous inputs must meet the specified setup and hold times for **ALL** rising edges of CLK when the chip is enabled. Chip enable must be valid at each rising edge of clock for the device (when \overline{TSP} or \overline{TSC} is low) to remain enabled.
6. 5 ns of setup delay is incurred in address buffers.

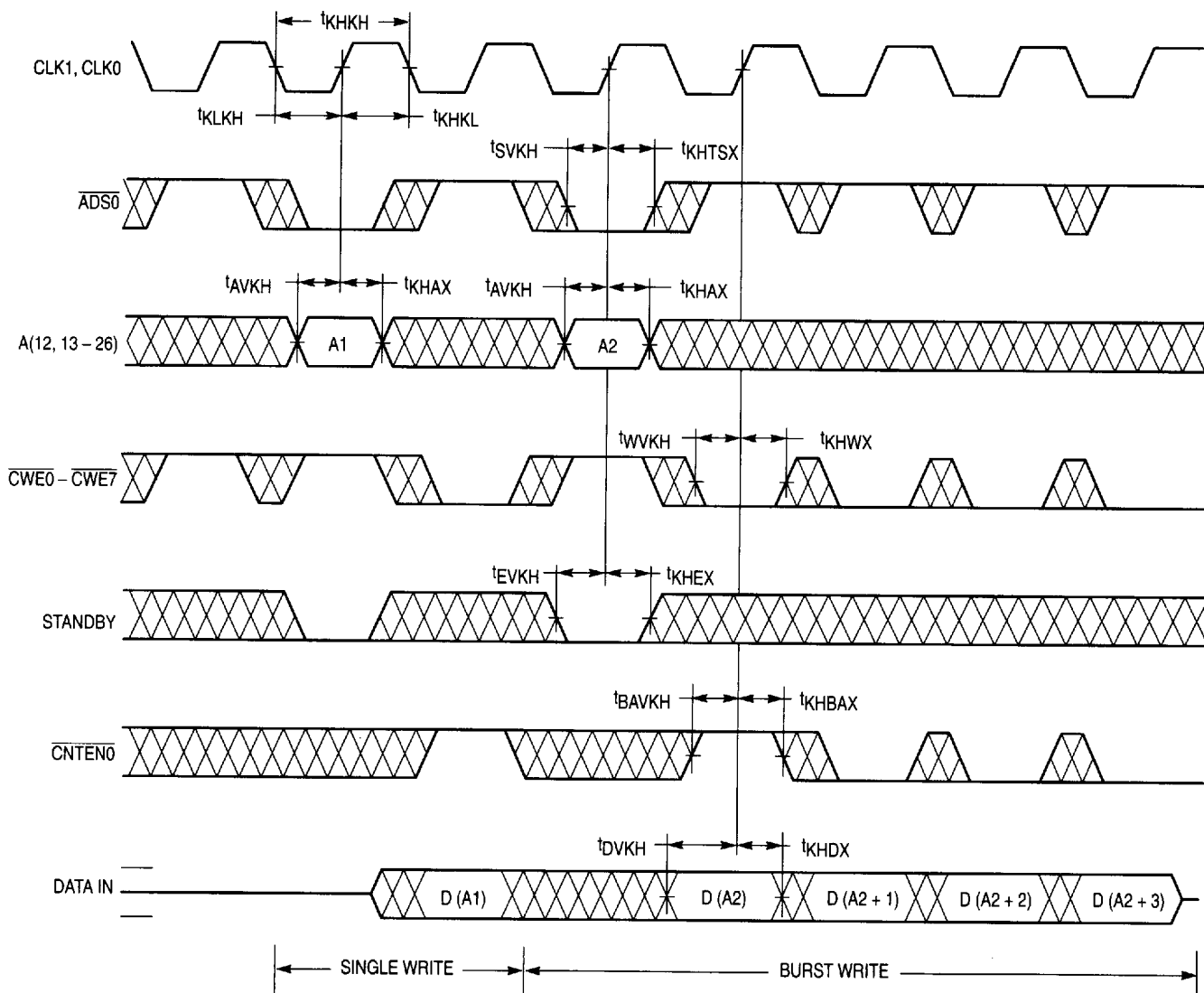
SYNCHRONOUS DATA RAM READ CYCLE



NOTES:

1. Cache addresses used are: 13 - 26 for MPC2105A; and 12 - 26 for MPC2106A.
2. Q1 (A2) represents the first output from the external address A2; Q2 (A2) represents the next output data in the burst sequence with A2 as the base address.

SYNCHRONOUS DATA RAM WRITE CYCLE



NOTES:

1. Cache addresses used are: 13 - 26 for MPC2105A; and 12 - 26 for MPC2106A.
2. $\overline{CG0} = V_{IH}$

TAG RAM

RESET FUNCTION TRUTH TABLE (See Notes 1 and 2)

TCLR	CLK	TWE	TAG0 – TAG11	DIRTYOUT	MATCH	Operation	POWER
L	L – H	H	High-Z	L ⁽³⁾	L ⁽³⁾	Reset Status	Active
L	L – H	L	—	—	—	Not Allowed	—

NOTES:

1. H = V_{IH}, L = V_{IL}, X = don't care, — = undefined.
2. \overline{TG} is X for this table.
3. These are output states.

READ FUNCTION TRUTH TABLE (See Notes 1, 2, and 3)

TG	TWE	CLK	TAG0 – TAG11	VALIDIN	DIRTYIN	DIRTYOUT	MATCH	Operation
L	H	X	D _{out}	—	—	D _{out}	D _{out}	Read Tag I/O
H	X	X	High-Z	—	—	—	—	Tag I/O Disable

WRITE FUNCTION TRUTH TABLE (See Notes 1 and 2)

TG	TWE	CLK	TAG0 – TAG11	VALIDIN	DIRTYIN	DIRTYOUT	MATCH	Operation
H	L	L – H	D _{in}	—	—	—	L	Write Tag I/O
L	L	L – H	—	—	—	—	—	Not Allowed

NOTES:

1. H = V_{IH}, L = V_{IL}, X = don't care, — = undefined.
2. This table applies when \overline{RESET} and \overline{PWRDN} are high.
3. D_{out} in this case is the same as D_{in}. The input data is written through to the outputs during the write operation.

MATCH FUNCTION TRUTH TABLE (See Notes 1 through 4)

TG	TWE	TAG0 – TAG11	VALIDIN ⁽⁴⁾	DIRTYIN ⁽⁴⁾	MATCH	Operation
X	X	—	—	—	D _{out}	Selected
L	H	D _{out}	—	—	L	Read Tag I/O
H	L	D _{in}	D _{in}	D _{in}	L	Write Tag I/O, Status Bits
H	H	TAG _{in}	L	—	L	Invalid Data – Dedicated Status Bits
H	H	TAG _{in}	H	—	H	Match – Dedicated Status Bits

NOTES:

1. H = V_{IH}, L = V_{IL}, X = don't care, — = undefined.
2. M = high if TAG_{in} equals the memory contents at the address; M = low if TAG_{in} does not equal the contents at that address.
3. \overline{PWRDN} and \overline{RESET} are high for this table. \overline{GS} and CLK are X.
4. This column represents the stored memory cell data for the given status bit at the selected address.

TAG RAM AC OPERATING CONDITIONS AND CHARACTERISTICS

(V_{CC} = 5.0 V ± 5%, T_A = 0 to + 70°C, Unless Otherwise Noted)

Input Timing Measurement Reference Level 1.5 V
 Input Pulse Levels 0 to 3.0 V
 Input Rise/Fall Time 3 ns

Output Timing Measurement Reference Level 1.5 V
 Output Load Figure 1A Unless Otherwise Noted

TAG RAM READ CYCLE (See Notes 1 through 4)

Parameter	Symbol	Tag RAM		Unit
		Min	Max	
Clock Access Time	t _{KHQV}	—	10	ns
Output Enable to Output Valid	t _{GLQV}	—	8	ns
Output Enable to Output Active	t _{GLQX}	0	—	ns
Output Disable to Q High-Z	t _{GHQZ}	1	6	ns
Status Bit Hold from Address Change	t _{AXSX}	3	—	ns
Address Access Time Status Bits	t _{AVSV}	—	10	ns
Tag Bit Hold from Address Change	t _{AVQX}	3	—	ns
Address Access Time Tag Bits	t _{AVQV}	—	12	ns

NOTES:

1. Setup and hold times, W (write) refers to \overline{TWE} .
2. A read cycle is defined by \overline{TWE} high. A write cycle is defined by \overline{TWE} low.
3. Maximum access times are guaranteed for all possible MC68040 and PowerPC external bus cycles.
4. Tag reads are asynchronous.

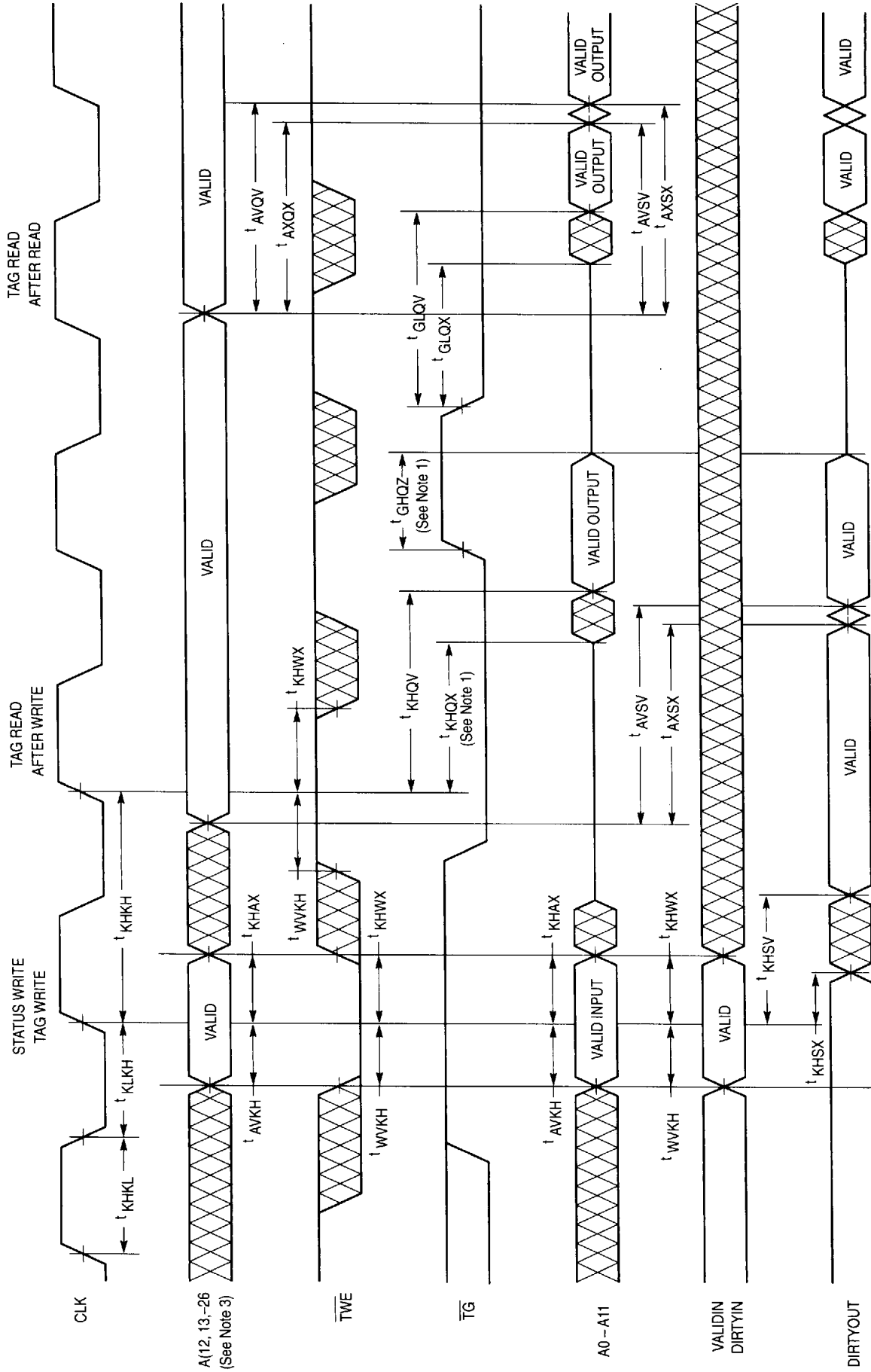
TAG RAM WRITE CYCLE (See Notes 1 through 4)

Parameter	Symbol	Tag RAM		Unit
		Min	Max	
Cycle Time	t _{KHKH}	15	—	ns
Clock High Pulse Width	t _{KHKL}	4.5	—	ns
Clock Low Pulse Width	t _{KLKH}	4.5	—	ns
Clock High to Output Active	t _{KHQX}	1.5	—	ns
Setup Times	Address	t _{AVKH}	3	ns
	Write	t _{WVKH}		
Hold Times	Address	t _{KHAX}	1.5	ns
	Write	t _{KHWX}		
Status Output Hold	t _{KHSX}	0	—	ns
Clock High to Status Bits Valid	t _{KHSV}	—	9	ns

NOTES:

1. Setup and hold times, W (write) refers to \overline{TWE} .
2. A read cycle is defined by \overline{TWE} high. A write cycle is defined by \overline{TWE} low.
3. Maximum access times are guaranteed for all possible MC68040 and PowerPC external bus cycles.
4. Tag writes are synchronous.

TAG RAM WRITE AND READ CYCLES (See Note 2)



NOTES:

1. Transition is measured plus or minus 200 mV from steady state.
2. \overline{TCLR} = High.
3. Cache addresses used are: A13 - 26 for MPC2105A, A12 - 26 for MPC2106A.

TAG RAM MATCH CYCLE

Parameter	Symbol	Tag RAM		Unit
		Min	Max	
Clock High Write to MATCH Invalid	t_{KHML}	—	7	ns
Clock High Read to MATCH Valid	t_{KHMV}	—	10	ns
Address Valid to MATCH Valid	t_{AVMV}	—	10	ns
MATCH Valid Hold from Address Change	t_{AXMX}	2	—	ns
\overline{TG} Low to MATCH Invalid	t_{GLML}	—	7	ns
\overline{TG} High to MATCH Valid	t_{GHMX}	—	8	ns

TAG RAM RESET (\overline{TCLR}) CYCLE

Parameter	Symbol	Tag RAM		Unit
		Min	Max	
\overline{TCLR} Setup Time	t_{STC}	4	—	ns
\overline{TCLR} Hold Time	t_{HTC}	1	—	ns
Status Bit Reset Time	t_{SRST}	—	60	ns
Status Bit Hold from \overline{TCLR} Low	t_{SHRS}	2	—	ns
\overline{TCLR} Low to MATCH Invalid	t_{RSML}	—	10	ns
\overline{TCLR} High to MATCH Valid	t_{RSMV}	—	100	ns
\overline{TCLR} Low to TAG High-Z	t_{RSQZ}	—	10	ns
\overline{TCLR} High to TAG Active	t_{RSQX}	—	100	ns
STANDBY Setup to \overline{TCLR} Low	t_{PDSR}	30	—	ns
\overline{TCLR} High to \overline{TWE} Low	t_{RHWX}	80	—	ns

AC TEST LOADS

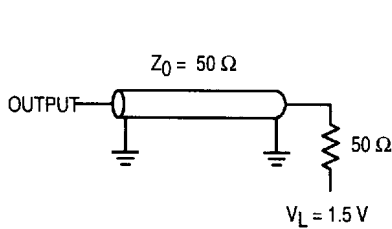


Figure 1A

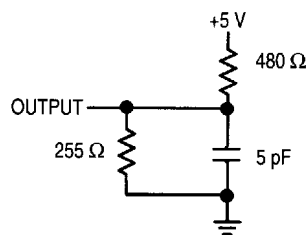
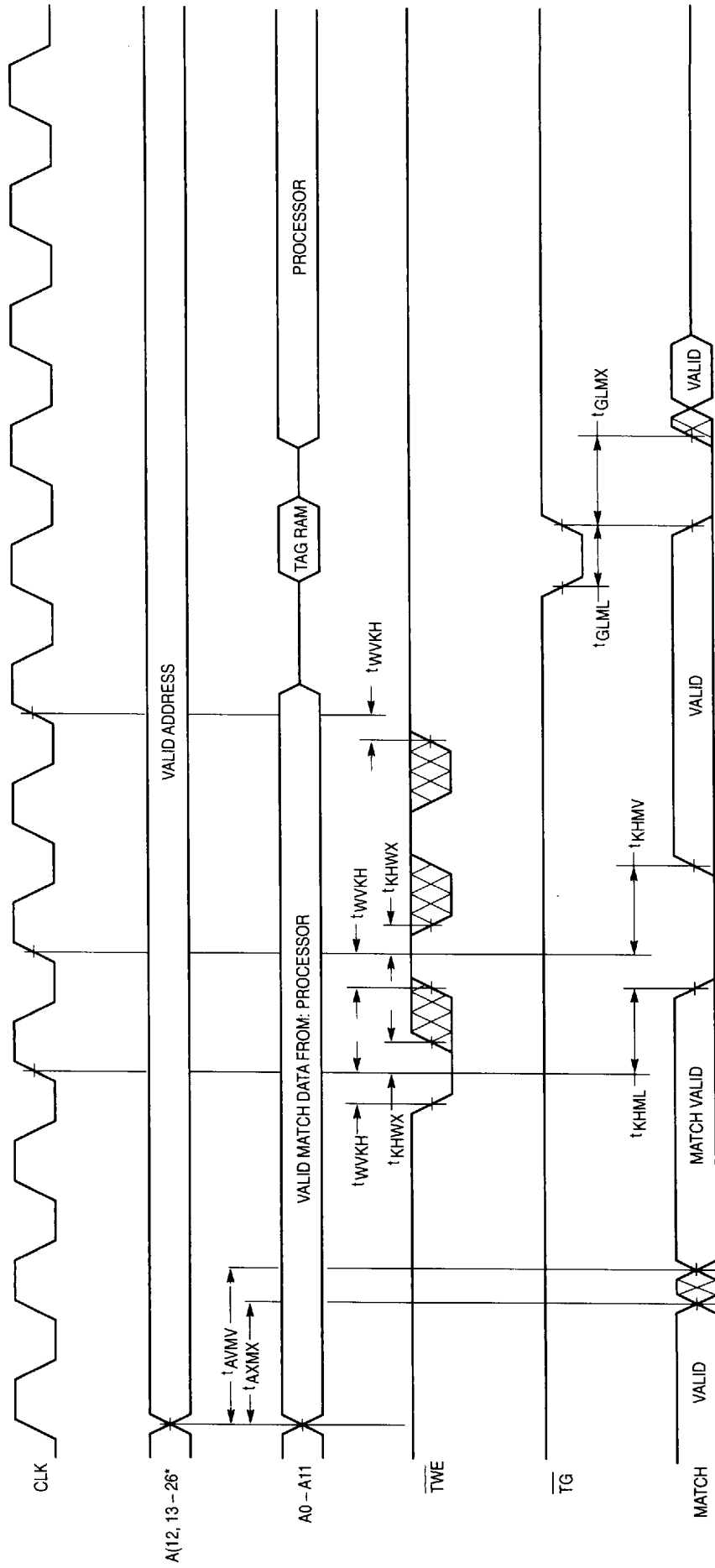


Figure 1B

TIMING LIMITS

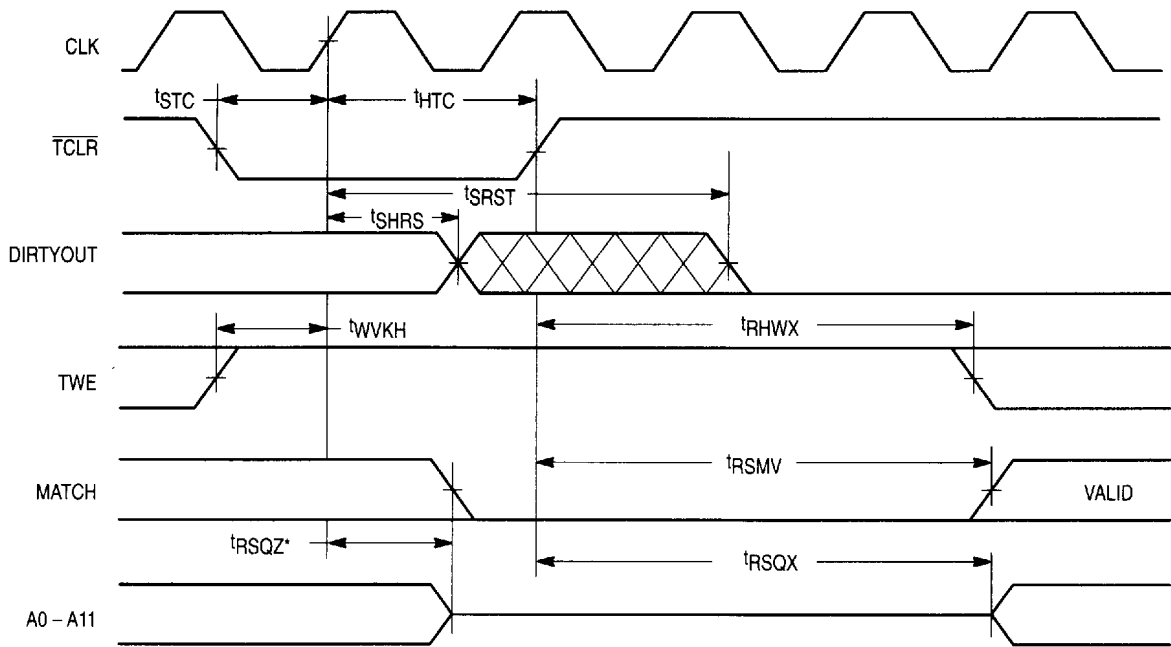
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

TAG RAM MATCH CYCLE



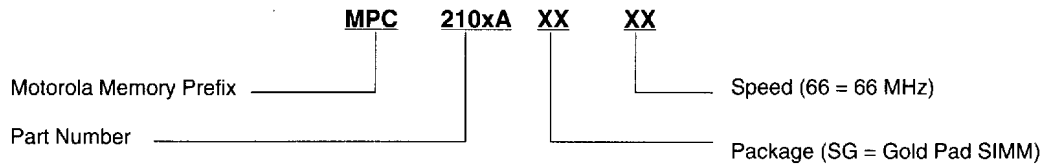
* Cache addresses used are: A13-26 for MPC2105A, A12-26 for MPC2106A.

TAG RAM $\overline{\text{TCLR}}$ FUNCTION



* Transition is measured plus or minus 200 mV from steady state.

ORDERING INFORMATION (Order by Full Part Number)



Full Part Numbers — MPC2105ASG66
MPC2106ASG66

MPC2105A = 512KB, synchronous
MPC2106A = 1MB, synchronous

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